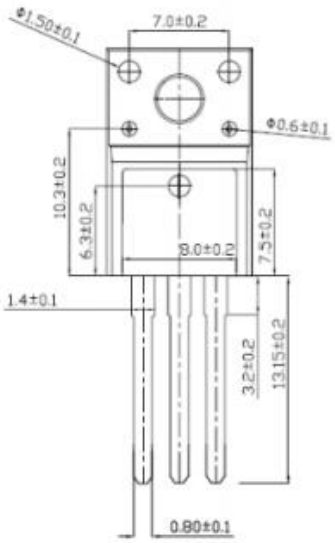
isc N-Channel MOSFET Transistor FQPF9N90C

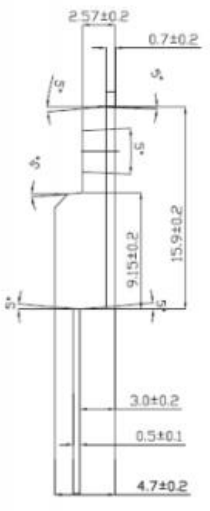
- **DESCRIPTION**
- RDS(on) = 1.4 Ω @VGS = 10 V, ID = 4 A
- Fast Switching Speed
- 100% Avalanche Tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

- **APPLICATIONS**
- General purpose power amplifier



- **ABSOLUTE MAXIMUM RATINGS(T_C=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	900	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ T_C=25℃	9	A
$I_{D(puls)}$	Pulse Drain Current	36	A
P_{tot}	Total Dissipation@T_C=25℃	30	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	4.17	℃/W

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D=250uA	900			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=250μA	3.0		5.0	V
V_{SD}	Diode Forward On-Voltage	I_S=8A ;V_{GS}= 0			1.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=4A			1.4	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 900V; V_{GS}= 0			1	μA